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Topological insulator with chiral edge state



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Topological insulator without magnetic field



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- Bi 111 bilayer ribbon is a 2D TI with helical edge states (Murakami, PRL 2006)



(111) Bi bilayer

- High SOI, key ingredient for TIs with TRS
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 5 Bi 111 bilayers is somewhat a 2D TI, surface states + 1D hinge states (Murani et al., Nat. Comm. 2017)

 >8 Bi 111 bilayers predicted not TI anymore (according to Liu et al., PRL 2011)









• The HOTI picture is recent, and it is not clear what to expect experimentally

Why using superconducting proximity effect ?



Why using superconducting proximity effect ?



Allow to:

- Reduce the contribution of diffusive states compared to the ballistic ones (phase coherence of the e-h pair required)
- Spatial distribution of the supercurrent through the junction with criticalcurrent-flux relation
 => is there 1D states ? Where ?
- Dependence of the energy on the superconducting phase with supercurrent-phase relation
 => are the states perfectly transmitted, with perfect crossing at φ = π as expected for topologically protected states ?

Sample fabrication



Bismuth nanowires:

- Previously grown by sputtering on a hot SiO2 substrate covered with a thin wetting layer and picked up and droped with a clean piece of wiper
 => nice ordered nanowires of D~200nm L~10um (IMT RAS, Chernogolovka)
- Now grown by sputtering on a cold substrate (reach ~70°), deposited with 10ns UV laser pulses
 => nice ordered nanowires of D~100nm L~20um, but potentially some strain
- Checked with Transmission Electron Microscope on the edges (IMT RAS, Chernogolovka)
- Selected and checked with Electron BackScattering Diffraction (ICMMO, Orsay)



Contacts:

- Superconducting contacts with disordered W deposited with Ga+ Focused Ion Beam, after etching => $T_c \leq 5 K$, $\Delta_0 \leq 1 \text{ meV}$ (CSNSM, Orsay)
- Larger metalic contacts with 200nm evaporated Au on top of 4nm of Ti











Superconducting proximity effect: Andreev Bound States

Resonance condition on accumulated phase: Andreev Bound States with eigenenergies ϵ_m



Superconducting proximity effect: Andreev Bound States

Resonance condition on accumulated phase: Andreev Bound States with eigenenergies $\epsilon_{
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largest current the superconducting system (symmetric SQUID) can support before becoming dissipative



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$$I_c \left(B + n \frac{\phi_0}{S} \right) = I_c(B)$$
$$\Delta B = \frac{\phi_0}{S}$$

Current of the whole junctions ΔB periodic

Supercurrent vs magnetic flux: many paths



Critical current vs flux: experiments



$L \gg W$ metalic case



Critical current vs flux: experiments on Bi

Ongoing experiment, ~100nm large Bi wire, 111 axis





=> Current carried by a small number of narrow paths

For previous experiments on Bi: Murani et al., Nat. Comm. 2017



100 nm EHT = 10.00 kV WD = 7.7 mm SE2 2.47e-004 Pa ICMWage

1D hinge states really topologically protected ?

Critical current vs flux measurement sensitive to the conduction channels geometry and distribution. Signature of topology other than the interference between a few channels at the edges of the sample ?

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Supercurrent vs phase

What is the behaviour of the S-Bi-S junction when we impose a phase bias ?



Supercurrent vs phase: topo vs trivial

What happens when there is scattering ?



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Kwon et al., Eur. Phys. J. B 2004



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Supercurrent vs phase: expectations



Supercurrent vs phase: measurement with an asymmetric SQUID

What happens when $\max I_a(\delta_a) \gg \max I_b(\delta_b)$?

Supports the largest current when $\delta_a = \theta$ is such that the current in I_a is maximum

$$I_c(B) = \max_{\delta_a} I_{tot}(\delta_a, B) \simeq I_{tot}(\theta, B)$$



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The big junction imposes $\delta_a = \theta$ and B imposes $\delta_b - \delta_a = 2\pi \frac{B.S}{\phi_0}$



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=> can measure supercurrent vs phase $I_b(\varphi)$ with $I_c(B)$ $I_c(B = \varphi \cdot \frac{\phi_0}{2\pi S}) \simeq I_a(\theta) + I_b(\theta + \varphi)$



Supercurrent vs phase: previous experiments

79.0

120

130





 $I_{c}(\mu A)$ 79.5 79.5

140

Murani et al., Nat. Comm. 2017

T=1.2 K

 $B_{z}(G)$

150

160

170

THANK YOU

Open questions

Can a big supercurrent be supported by many hinge states arranged in steps ?



(a)

m(y) < 0

m(y) > 0

m(y) < 0

hinge e

|↓ 2e

hinge 1

hinge 2

(b)

R. S. Deacon Ishibashi's group, RIKEN



80 meV

-120 meV

-280 meV

High dI/dV (au) Low

45

What is the effect of defects on the surface of Bi ? What about strain ? Revealing topological nature with screw dislocations ? (Nayak et al., Cond. Mat. 2019)

What happens at high magnetic field ? (Queiroz and Stern, Cond. Mat. 2019)

